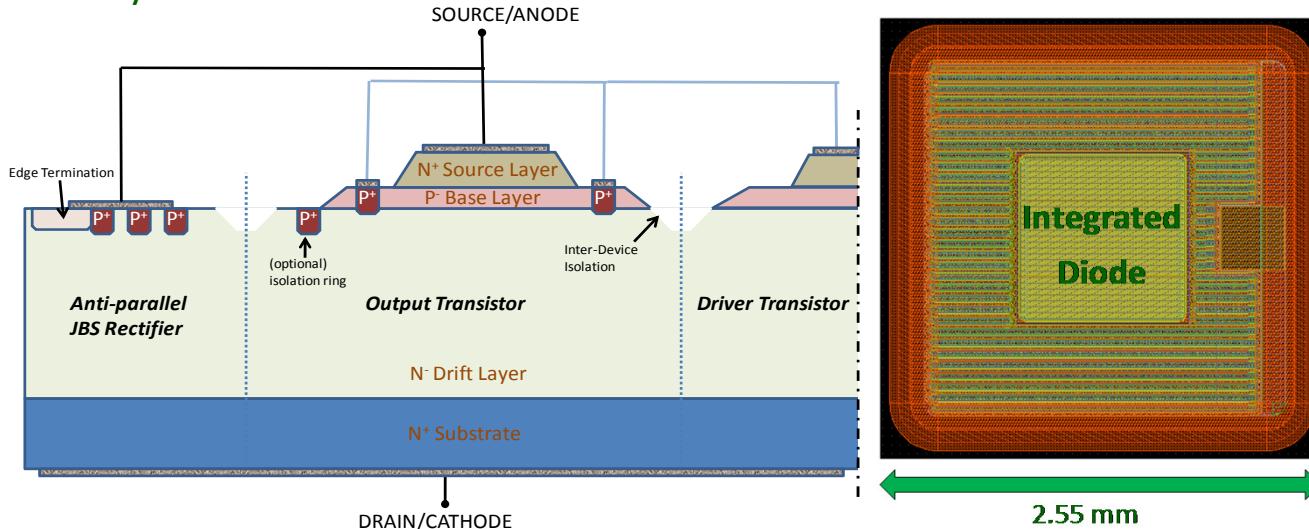


### *Overall Program Goal*

Develop the device designs and process technology for constructing 15 kV/10 A integrated SiC Junction Transistor-Rectifier devices targeted for insertion into medium voltage power electronics.

### *Acknowledgement*

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- If achieved it will be the first time a high voltage integrated circuit is demonstrated in SiC
- Universal applicability towards all grid-connected power electronics

### *Current Status*

- Conducting 2-D Simulations
- Designing mask layouts
- Performing unit process development

### *Future Steps*

- Mask Plate Production
- Prototype Fabrication
- On-wafer characterization